

MMPQ2222

NPN Multi-Chip General Purpose Amplifier

- This device is for use as a medium power amplifier and switch requiring collector currents up to 500mA.
- Sourced from process 19.



Absolute Maximum Ratings * T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +155	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics	•	•		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_C = 10\mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		50	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3.0V, I _C = 0		50	nA
On Charact	eristics *	•	•	•	
h _{FE}	DC Current Gain	I _C = 10mA, V _{CE} = 10V I _C = 150mA, V _{CE} = 1.0V * I _C = 150mA, V _{CE} = 1.0V *	75 100 50		
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$		0.4 1.6	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage *	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$		1.3 2.6	V V
Small Signa	I Characteristics				,
f _T	Current GAin Bandwidth Product	$I_C = 20 \text{mA}, V_{CE} = 20 \text{V},$ f = 100MHz		300	MHz
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 100kHz$		4.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5V, I_{E} = 0, f = 100kHz$		20	pF
NF	Noise Figure	$I_C = 100\mu A, V_{CE} = 10V,$ $R_S = 1.0k\Omega, f = 1.0kHz$		2.0	dB

^{*} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Symbol	Parameter	Max.	Units
P_{D}	Total Device Dissipation	1000	mW
_	Derate above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		
0071	Effective 4 Die	125	°C/W
	Each Die	240	°C/W

Typical Characteristics

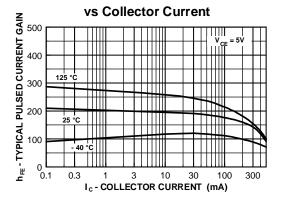


Figure 1. Typical Pulsed Current Gain vs Collector Current

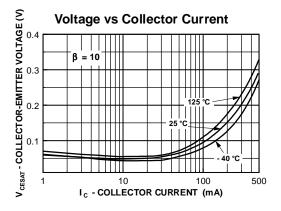


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

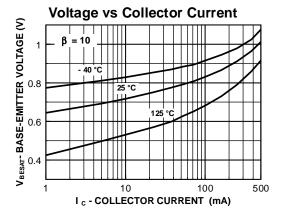


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

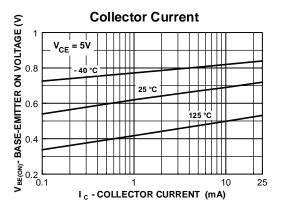


Figure 4. Base-Emitter On Voltage vs Collector Current

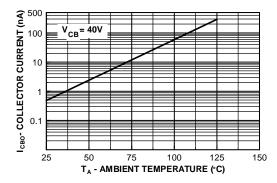


Figure 5. Collector Cutoff Current vs Ambient Temperature

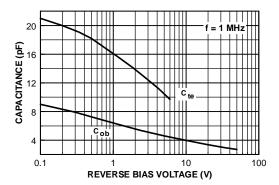


Figure 6. Emitter Transition and Output Capacitance vs Reverse Bias Voltage

Typical Characteristics (Continued)

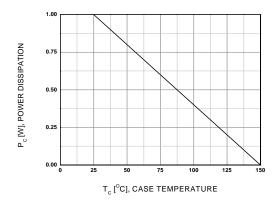


Figure 7. Power Dissipation vs Ambient Temperature

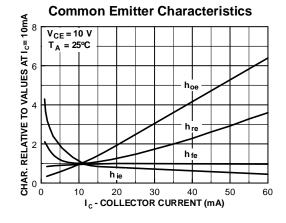


Figure 8. Common Emitter Characteristics

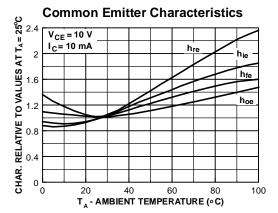


Figure 9. Common Emitter Characteristics

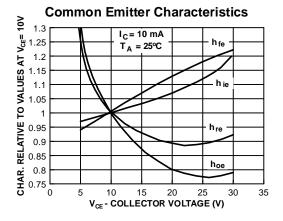


Figure 10. Common Emitter Characteristics

Test Circuit

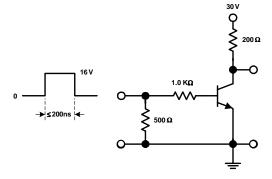


Figure 1. Saturated Turn-On Switching Time

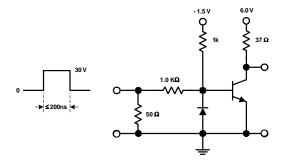
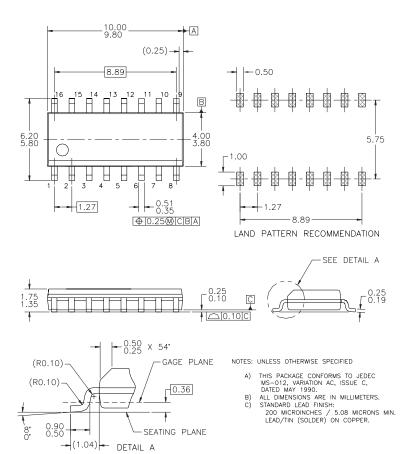


Figure 2. Saturated Turn-Off Switching Time

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Package Dimensions

SOIC-16



Dimensions in Millimeters

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